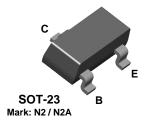


# **PN200 PN200A**

# **MMBT200** MMBT200A





# **PNP General Purpose Amplifier**

This device is designed for general purpose amplifier applications at collector currents to 300 mA. Sourced from Process 68.

#### **Absolute Maximum Ratings\*** TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CEO}$	Collector-Emitter Voltage	45	V
V <sub>CBO</sub>	Collector-Base Voltage	60	V
V <sub>EBO</sub>	Emitter-Base Voltage	6.0	V
I <sub>C</sub>	Collector Current - Continuous	500	mA
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

<sup>\*</sup>These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
  2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.
- 3) All voltages (V) and currents (A) are negative polarity for PNP transistors.

#### **Thermal Characteristics** TA = 25°C unless otherwise noted

Symbol	Characteristic	M	ax	Units
		PN200 PN200A	*MMBT200 *MMBT200A	
P <sub>D</sub>	Total Device Dissipation	625	350	mW
	Derate above 25°C	5.0	2.8	mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3		°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	357	°C/W

<sup>\*</sup>Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

# **PNP General Purpose Amplifier**

(continued)

## Electrical Characteristics TA = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
OFFICHAE	DACTEDISTICS				
	RACTERISTICS	T		1	
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	$I_C = 10 \mu\text{A},  I_B = 0$	60		V
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage*	$I_C = 1.0 \text{ mA}, I_E = 0$	45		V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	$I_E = 10 \mu\text{A},  I_C = 0$	6.0		V
I <sub>CBO</sub>	Collector Cutoff Current	$V_{CB} = 50 \text{ V}, I_{E} = 0$		50	nA
I <sub>CES</sub>	Collector Cutoff Current	V <sub>CE</sub> = 40 V, I <sub>E</sub> = 10		50	nA
I <sub>EBO</sub>	Emitter Cutoff Current	$V_{EB} = 4.0 \text{ V}, I_{C} = 0$		50	nA

#### **ON CHARACTERISTICS**

h <sub>FE</sub>	DC Current Gain	$I_C = 100 \mu A, V_{CE} = 1.0 V$	200	80		
		$I_C = 10 \text{ mA}, V_{CE} = 1.0 \text{ V}$	200A 200 200A	240 100 300	450 600	
		$I_C = 100 \text{ mA}, V_{CE} = 1.0 \text{ V}^*$ $I_C = 150 \text{ mA}, V_{CE} = 5.0 \text{ V}^*$	200A 200 200A	100 100 100	350	
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 10 mA, I <sub>B</sub> = 1.0 mA I <sub>C</sub> = 200 mA, I <sub>B</sub> = 20 mA*			0.2 0.4	V V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	$I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$ $I_C = 200 \text{ mA}, I_B = 20 \text{ mA}^*$			0.85 1.0	V V

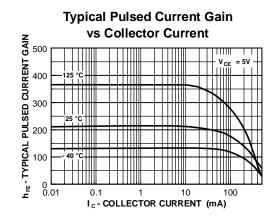
#### SMALL SIGNAL CHARACTERISTICS

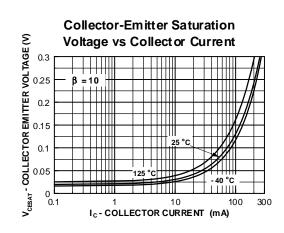
f <sub>T</sub>	Current Gain - Bandwidth Product	$V_{CE} = 20 \text{ V}, I_{C} = 20 \text{ mA}$	250		MHz
C <sub>obo</sub>	Output Capacitance	V <sub>CB</sub> = 10 V, f = 1.0 MHz		6.0	pF
NF	Noise Figure	$I_C = 100 \mu\text{A},  V_{CE} = 5.0 \text{V},$		4.0	dB
		$R_G = 2.0 \text{ k}\Omega, f = 1.0 \text{ kHz}$		4.0	dB

<sup>\*</sup>Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2.0%

NOTE: All voltages (V) and currents (A) are negative polarity for PNP transistors.

# **Typical Characteristics**

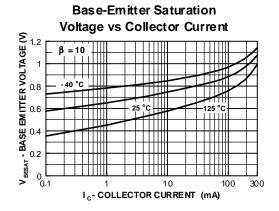


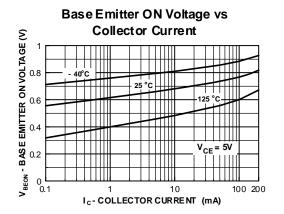


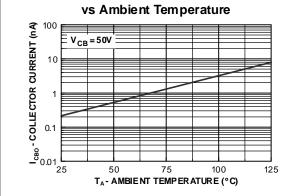
## **PNP General Purpose Amplifier**

(continued)

## Typical Characteristics (continued)

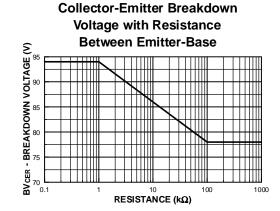


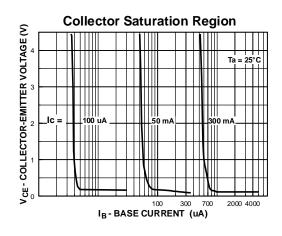


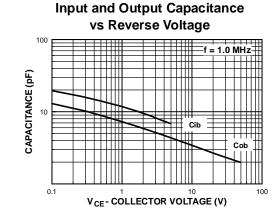


TA- AMBIENT TEMPERATURE (°C)

Collector-Cutoff Current



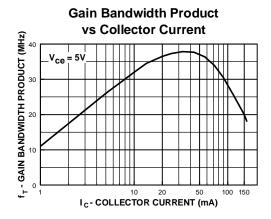


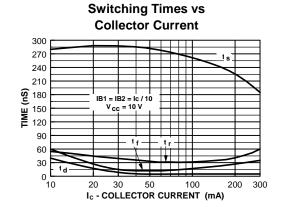


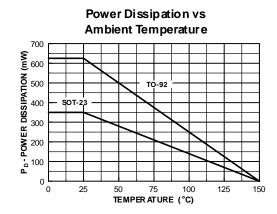
# **PNP General Purpose Amplifier**

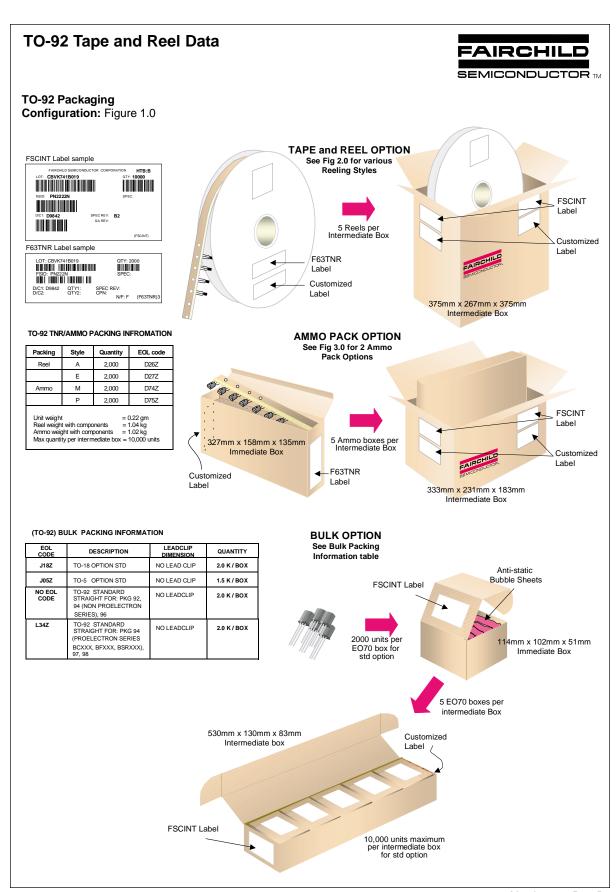
(continued)

## Typical Characteristics (continued)







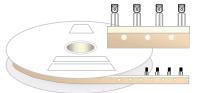


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# TO-92 Tape and Reel Data, continued

# **TO-92 Reeling Style Configuration:** Figure 2.0

#### Machine Option "A" (H)



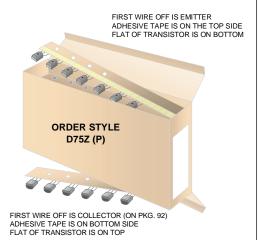
Style "A", D26Z, D70Z (s/h)

# Machine Option "E" (J)

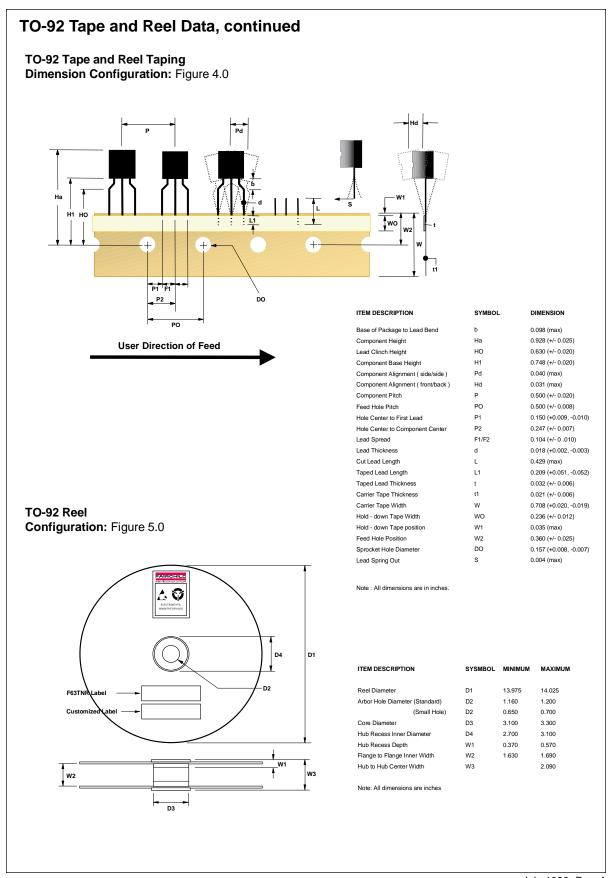
Style "E", D27Z, D71Z (s/h)

# **TO-92 Radial Ammo Packaging Configuration:** Figure 3.0





September 1999, Rev. B

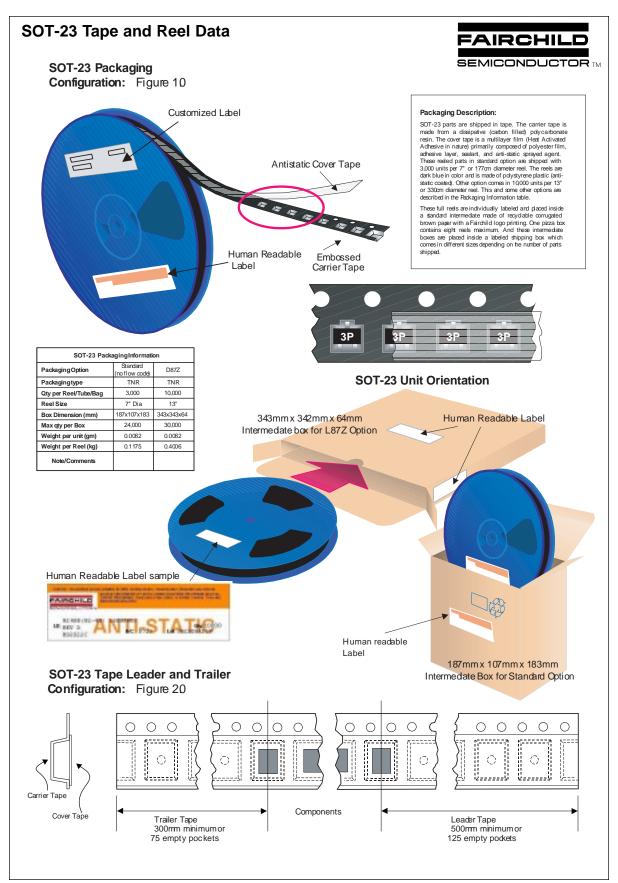


# **TO-92 Package Dimensions** FAIRCHILD SEMICONDUCTOR TM TO-92 (FS PKG Code 92, 94, 96) Scale 1:1 on letter size paper Dimensions shown below are in: inches [millimeters] Part Weight per unit (gram): 0.1977 0.185 4.70 0.170 4.32 TO-92 (92,94,96) 94 96 B F В В В D D 2 В S С G Ε Ø0.060 [Ø1.52] G В S С G 0.010 [0.254] DEEP 5.0°TYP.

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0.095 0.084 2.13

January 2000, Rev. B

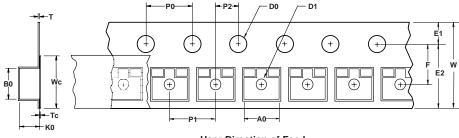


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# SOT-23 Tape and Reel Data, continued

## **SOT-23 Embossed Carrier Tape**

Configuration: Figure 3.0



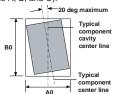
User Direction of Feed	

	Dimensions are in millimeter													
Pkg type	Α0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	Т	Wc	Тс
<b>SOT-23</b> (8mm)	3.15 +/-0.10	2.77 +/-0.10	8.0 +/-0.3	1.55 +/-0.05	1.125 +/-0.125	1.75 +/-0.10	6.25 min	3.50 +/-0.05	4.0 +/-0.1	4.0 +/-0.1	1.30 +/-0.10	0.228 +/-0.013	5.2 +/-0.3	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation



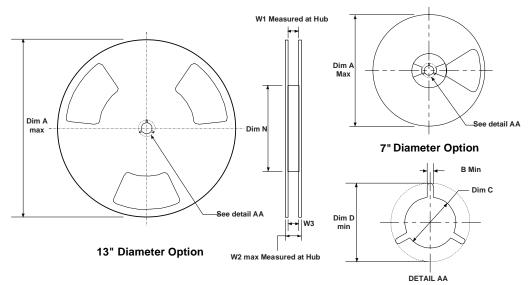
Sketch B (Top View)
Component Rotation



Sketch C (Top View)

Component lateral movement

### SOT-23 Reel Configuration: Figure 4.0

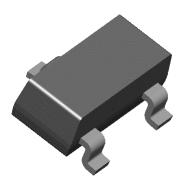


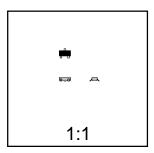
	Dimensions are in inches and millimeters								
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
8mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9
8mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9

# **SOT-23 Package Dimensions**



# SOT-23 (FS PKG Code 49)

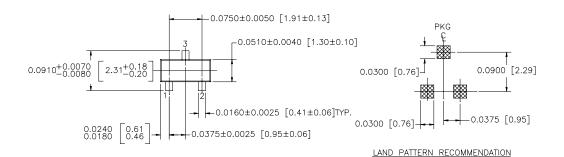


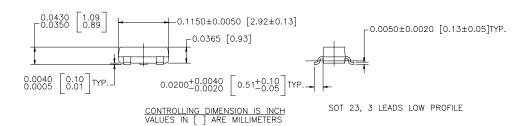


Scale 1:1 on letter size paper

Dimensions shown below are in: inches [millimeters]

Part Weight per unit (gram): 0.0082





NOTE: UNLESS OTHERWISE SPECIFIED

- 1. STANDARD LEAD FINISH 150 MICROINCHES / 3.81 MICROMETERS MINIMUM TIN / LEAD (SOLDER) ON ALLOY 42
- 2. REFERENCE JEDEC REGISTRATION TO-236, VARIATION AB, ISSUE G, DATED JUL 1993

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